

Yasunori Tokuda

List of Publications by Year in descending order

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papers

1,146
citations

430874

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454955

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97
all docs

97
docs citations

97
times ranked

805
citing authors

#	ARTICLE	IF	CITATIONS
1	Nondestructive mixing characteristics of optical resonance modes investigated using artificial dielectric systems. AIP Advances, 2020, 10, .	1.3	0
2	Marked effects of lateral displacement on the optical transmission properties of stacked artificial dielectric systems composed of metallic sub-wavelength slit arrays. Japanese Journal of Applied Physics, 2019, 58, 122004.	1.5	2
3	Insertion effects of natural dielectric between artificial dielectrics formed by metallic sub-wavelength slit arrays. AIP Advances, 2018, 8, .	1.3	3
4	Waveguide resonance mode response of stacked structures of metallic sub-wavelength slit arrays. Journal of Applied Physics, 2018, 123, .	2.5	6
5	Quasi-dielectric characteristics of stacked metallic metamaterials. Japanese Journal of Applied Physics, 2017, 56, 030306.	1.5	0
6	Multiple intersection properties of optical resonance modes in metallic metamaterials. AIP Advances, 2017, 7, .	1.3	4
7	Fast beam switching operation of two-dimensional microcavity laser diode. , 2016, , .		1
8	Crossing behaviors of optical resonance modes in metallic metamaterials. Applied Physics Express, 2016, 9, 032201.	2.4	7
9	Transverse magnetic emissions of GaAs unstrained quantum-well microcavity lasers. , 2015, , .		0
10	Light propagation in a Penrose unilluminable room. Optics Express, 2015, 23, 17431.	3.4	4
11	Compact Two-Dimensional Multipass GaAs Optical Cavity with a Long Path Length. , 2014, , .		0
12	Lasing of TM modes in a two-dimensional GaAs microlaser. Optics Express, 2014, 22, 11912.	3.4	6
13	Crossover from capacitive to inductive electromagnetic responses in near self-complementary metallic checkerboard patterns. Optics Express, 2014, 22, 24787.	3.4	27
14	Investigation of fade-out mechanism of resonance modes in optical transmission using stacked metallic sub-wavelength slit arrays. Journal of Applied Physics, 2014, 115, 243104.	2.5	8
15	Analysis of resonator modes in two-dimensional laser cavities containing a left-handed material. Optical Review, 2013, 20, 293-295.	2.0	0
16	AlGaIn Channel HEMT With Extremely High Breakdown Voltage. IEEE Transactions on Electron Devices, 2013, 60, 1046-1053.	3.0	108
17	Selective excitation of lowest-order transverse ring modes in a quasi-stadium laser diode. Optics Letters, 2013, 38, 4158.	3.3	4
18	Tuning the effective refractive index of a thin air gap region sandwiched by metallic metamaterials by lateral displacements. Journal of Applied Physics, 2013, 113, .	2.5	7

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19	Spectroscopic Functions of Multi-Stacked Metallic Plates with Modulated Slit Arrays. Applied Physics Express, 2013, 6, 062602.	2.4	9
20	Ray Dynamical Simulation of Penrose Unilluminable Room Cavity. , 2013, , .		2
21	Lowest-order axial and ring mode lasing in confocal quasi-stadium laser diodes. Applied Optics, 2012, 51, 2515.	1.8	11
22	Optical Phased Array Functions in Double-Layered Metallic Plate Systems with Artificially Modulated Slit Arrays. Applied Physics Express, 2012, 5, 042502.	2.4	12
23	Remarkable transmission characteristics of optical waves through modulated double-layered metallic slit arrays. AIP Advances, 2012, 2, 042112.	1.3	7
24	Quality factor of circular laser diode beam tailored by optical interference. Optical Review, 2012, 19, 328-331.	2.0	0
25	Enhancement of Drain Current by an AlN Spacer Layer Insertion in AlGaN/GaN High-Electron-Mobility Transistors with Si-Ion-Implanted Source/Drain Contacts. Japanese Journal of Applied Physics, 2011, 50, 064101.	1.5	20
26	Resonator Modes of Quasi-Stadium Laser Diodes with Unstable Optical Cavities. The Review of Laser Engineering, 2011, 39, 537-542.	0.0	0
27	Laser diode beam shaping by optical interference. Optical Review, 2011, 18, 287-292.	2.0	3
28	Quality factor of laser diode beam tailored by Lloyd's mirror interference. , 2011, , .		0
29	Selective excitation of lowest-order axial and ring modes in confocal quasi-stadium laser diodes. , 2011, , .		0
30	Enhancement of Drain Current by an AlN Spacer Layer Insertion in AlGaN/GaN High-Electron-Mobility Transistors with Si-Ion-Implanted Source/Drain Contacts. Japanese Journal of Applied Physics, 2011, 50, 064101.	1.5	20
31	Analysis of Single-Photon-Detection Characteristics of GaInAs/InP Avalanche Photodiodes. IEEE Journal of Quantum Electronics, 2010, 46, 1444-1449.	1.9	9
32	Optical transmission anomalies in a double-layered metallic slit array. Optics Express, 2010, 18, 17876.	3.4	25
33	Fabrication of Terahertz Planar Metamaterials Using a Super-Fine Ink-Jet Printer. Applied Physics Express, 2010, 3, 016701.	2.4	64
34	Resonator modes in a two-dimensional quasi-stadium laser diode with concave end mirrors. , 2010, , .		0
35	Look out III-V. Nature Photonics, 2009, 3, 7-8.	31.4	8
36	Design and Characteristics of Guardring-Free Planar AlInAs Avalanche Photodiodes. Journal of Lightwave Technology, 2009, 27, 1011-1017.	4.6	18

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37	Remarkable breakdown voltage enhancement in AlGa _N channel high electron mobility transistors. Applied Physics Letters, 2008, 92, .	3.3	132
38	Planar Avalanche Photodiode for Long-Haul Single-Photon Optic Fiber Communications. Applied Physics Express, 2008, 1, 012001.	2.4	2
39	First Operation of AlGa _N Channel High Electron Mobility Transistors. Applied Physics Express, 2008, 1, 011101.	2.4	71
40	Lasing Mechanism Analysis of Self-Pulsating Distributed Feedback Laser Diodes and Successful Demonstration of All-Optical Signal Recovery at 40 Gbps. Japanese Journal of Applied Physics, 2008, 47, 3493-3498.	1.5	1
41	X-ray Photoelectron Spectroscopy Study of the Origin of the Improved Device Performance by a Thin Al Layer Insertion between AlGa _N and Schottky Gate on the AlGa _N /Ga _N High-Electron-Mobility Transistor. Japanese Journal of Applied Physics, 2007, 46, L584-L586.	1.5	1
42	Degradation Mode Analysis on Highly Reliable Guardring-Free Planar InAlAs Avalanche Photodiodes. Journal of Lightwave Technology, 2007, 25, 3686-3693.	4.6	29
43	Remarkable Breakdown Voltage Enhancement in AlGa _N Channel HEMTs. , 2007, , .		11
44	Guardring-Free Planar AlInAs Avalanche Photodiodes for 2.5-Gb/s Receivers With High Sensitivity. IEEE Photonics Technology Letters, 2007, 19, 765-767.	2.5	4
45	Ion implantation doping for AlGa _N /Ga _N HEMTs. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 2364-2367.	0.8	27
46	All-Optical Clock Recovery and Wavelength Conversion by Combination of Self-Pulsation Laser and Semiconductor-Optical-Amplifier-Based Mach-Zehnder Interferometer. Japanese Journal of Applied Physics, 2006, 45, 3457-3461.	1.5	1
47	Thermal robustness in synthetic antiferromagnetic free layer for magnetic random access memory applications. Journal of Applied Physics, 2006, 99, 08C911.	2.5	3
48	Effects of a thin Al layer insertion between AlGa _N and Schottky gate on the AlGa _N -Ga _N high electron mobility transistor characteristics. Applied Physics Letters, 2006, 88, 043503.	3.3	20
49	Efficient incorporation of a nonnatural amino acid into a protein in an insect cell-free translation system. Nucleic Acids Symposium Series, 2006, 50, 277-278.	0.3	3
50	Very High Frequency Self-Pulsation and Stable Optical Injection Locking for Well-Defined Multi-Electrode Distributed Feedback Lasers. Japanese Journal of Applied Physics, 2004, 43, 1965-1968.	1.5	4
51	Self-pulsation and optical injection locking for multielectrode distributed feedback lasers using phase-shift-induced modes. Applied Physics Letters, 2004, 85, 4840-4841.	3.3	8
52	Improvement of alignment tolerance against contact hole etching by growing of underlying silicon-selective epitaxial layer. Microelectronic Engineering, 2001, 56, 281-287.	2.4	1
53	Low thermal budget surface cleaning after dry etching for selective silicon epitaxial growth. Journal of Crystal Growth, 2001, 226, 443-450.	1.5	12
54	A Dual-Gate Complementary Metal-Oxide-Semiconductor Technology with Novel Self-Aligned Pocket Implantation which Takes Advantage of Elevated Source/Drain Configurations. Japanese Journal of Applied Physics, 2001, 40, 2611-2615.	1.5	1

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55	Remarkable Effects of Introduction of SiON Materials into Shallow Trench Isolation Fabrication Process on Metal-Oxide-Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2001, 40, 462-466.	1.5	2
56	Surface Defect Formation in Epitaxial Si Grown on Boron-Doped Substrates by Ultrahigh Vacuum Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2001, 40, L1051-L1053.	1.5	0
57	Epitaxial Si _{1-x} Ge _x grown into fine contact hole by ultrahigh-vacuum chemical vapor deposition. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 68, 171-174.	3.5	7
58	Selective Epitaxial Growth by Ultrahigh-Vacuum Chemical Vapor Deposition with Alternating Gas Supply of Si ₂ H ₆ and Cl ₂ . Japanese Journal of Applied Physics, 2000, 39, 6139-6142.	1.5	4
59	Parasitic Resistance Reduction in Deep Submicron Dual-Gate Transistors with Partially Elevated Source/Drain Extension Regions Fabricated by Complementary Metal-Oxide-Semiconductor Technologies. Japanese Journal of Applied Physics, 2000, 39, 387-389.	1.5	21
60	Advantage of Shallow Trench Isolation over Local Oxidation of Silicon on Alignment Tolerance. Japanese Journal of Applied Physics, 1999, 38, L234-L235.	1.5	10
61	Si Deposition into Fine Contact Holes by Ultrahigh-Vacuum Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1999, 38, 4045-4046.	1.5	7
62	Significant Effects of As Ion Implantation on Si-selective Epitaxy by Ultrahigh Vacuum Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1999, 38, 5046-5047.	1.5	8
63	Experimental study on isolation edge effects in the short channel characteristics of metal oxide semiconductor field effect transistors (MOSFETs). Microelectronic Engineering, 1999, 45, 369-375.	2.4	0
64	Anomalous Gate Length Dependence of Threshold Voltage of Trench-Isolated Metal Oxide Semiconductor Field Effect Transistors. Japanese Journal of Applied Physics, 1998, 37, L852-L854.	1.5	4
65	Protection of Field Oxide in Trench Isolation against Contact Hole Etching to Improve Alignment Tolerance. Japanese Journal of Applied Physics, 1998, 37, L833-L835.	1.5	2
66	Narrow-Channel Metal Oxide Semiconductor Field Effect Transistor (MOSFET) Isolated by an Ultra-Fine Trench. Japanese Journal of Applied Physics, 1997, 36, L547-L549.	1.5	3
67	Characterization of Crystallinity in Low-Temperature-Grown GaAs Layers by Raman Scattering and Time-Resolved Photoreflectance Measurements. Japanese Journal of Applied Physics, 1996, 35, 5955-5963.	1.5	14
68	Electrical Characteristics of Ultra-Fine Trench Isolation Fabricated by a New Two-Step Filling Process. Japanese Journal of Applied Physics, 1996, 35, L1625-L1627.	1.5	2
69	Spectroscopic Characterization of Low-Temperature Grown GaAs Epitaxial Films. Japanese Journal of Applied Physics, 1994, 33, 4807-4811.	1.5	43
70	Multistable behavior of connected bistable devices. Journal of Applied Physics, 1994, 75, 3749-3755.	2.5	10
71	External bias voltage and incident light intensity dependent effects of quantum-confined excitonic transitions on bulk background photocurrent spectra. Journal of Applied Physics, 1994, 75, 1620-1622.	2.5	1
72	All-optical bistability of a p-i-p-i-n device with GaAs/AlAs coupled-quantum-well absorption layers and an AlAs resistive layer. Optics Letters, 1993, 18, 885.	3.3	2

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73	Optical bistable responses based on self-electro-optic effect in a nonbiased asymmetric coupled quantum well photodiode. Applied Physics Letters, 1993, 62, 2492-2494.	3.3	8
74	Optically reversible switching between binary states using multistable loops. Applied Physics Letters, 1993, 63, 2609-2611.	3.3	4
75	Significant effect of lateral resistivity on optical nonlinear responses of a quantum well photodiode. Applied Physics Letters, 1993, 63, 3259-3261.	3.3	8
76	Optical nonlinear responses of a quantum well photodiode with a nonohmic contact. Applied Physics Letters, 1992, 60, 1664-1666.	3.3	3
77	Room-Temperature Self-Electrooptic Effects of GaAs/AlAs Asymmetric Coupled Quantum Wells. Japanese Journal of Applied Physics, 1991, 30, L963-L965.	1.5	0
78	Triple excitonic mixing associated with recoupling of a Stark-localized state in coupled quantum wells confined by superlattices. Physical Review B, 1991, 43, 7170-7173.	3.2	9
79	Complex multistable responses of serially connected optical bistable devices. Applied Physics Letters, 1991, 59, 1016-1018.	3.3	7
80	Step-Promoted Surface Reconstruction on Ga-Deposited (100) GaAs During Molecular Beam Epitaxy with Alternating Supply of Ga and As. Japanese Journal of Applied Physics, 1991, 30, 3491-3495.	1.5	4
81	Self-electro-optic effect based on anticrossing of excitonic transitions in a coupled quantum well structure. Applied Physics Letters, 1990, 56, 166-167.	3.3	26
82	Novel spectral response of a coupled quantum well photodiode. Applied Physics Letters, 1990, 56, 2166-2168.	3.3	6
83	Observation of excitonic effects on electroabsorption in coupled quantum wells. Physical Review B, 1990, 41, 10280-10282.	3.2	19
84	Dual-wavelength multiple quantum well photodetector using an optically bistable abrupt absorption edge. Applied Physics Letters, 1990, 56, 227-229.	3.3	9
85	Distinct observation of interwell coupling effect on optical transitions in double quantum wells in an electric field. Applied Physics Letters, 1989, 54, 1232-1234.	3.3	34
86	Incident wavelength dependence of photocurrent bistability by external bias voltage control in a quantum well photodiode. Applied Physics Letters, 1989, 55, 711-712.	3.3	4
87	Self-deformed and hysteretic photocurrent spectra of quantum wells with a load resistor. Applied Physics Letters, 1989, 54, 2324-2326.	3.3	9
88	Photoluminescence of a Novel Heteron-i-p-i Structure Incorporating Triple Quantum Wells. Japanese Journal of Applied Physics, 1989, 28, L747-L749.	1.5	2
89	Anomalous excitation intensity dependence of photoluminescence properties of an asymmetric coupled quantum well structure. Journal of Applied Physics, 1989, 65, 2168-2170.	2.5	14
90	Emission spectra of single quantum well lasers with inhomogeneous current injection. Journal of Applied Physics, 1988, 64, 1022-1026.	2.5	13

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91	Dual-wavelength emission from a twin-stripe single quantum well laser. Applied Physics Letters, 1987, 51, 1664-1666.	3.3	10
92	Lasng wavelength of an asymmetric double quantum well laser diode. Applied Physics Letters, 1987, 51, 209-211.	3.3	10
93	Carrier-Temperature and Wavelength-Switching in GaAs Single-Quantum-Well Baser Diode. Japanese Journal of Applied Physics, 1986, 25, L931-L933.	1.5	4
94	On the Origin of Oval Defect with Nucleus on Epilayers Grown by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1986, 25, 908-909.	1.5	10
95	Widely separate wavelength switching of single quantum well laser diode by injection-current control. Applied Physics Letters, 1986, 49, 1629-1631.	3.3	29
96	Application of AlAs-GaAs superlattices to step-index and graded-index waveguide separate-confinement heterostructure laser diodes. Journal of Applied Physics, 1986, 60, 2729-2734.	2.5	20
97	Drivability Enhancement for AlGaN/GaN High-Electron Mobility Transistors with AlN Spacer Layer Using Si Ion Implantation Doping. Applied Physics Express, 0, 2, 031003.	2.4	18